IN THE CLAIMS

Please amend the claims as follows:

1. (Once amended.) A semiconductor laser light emitting device comprising:

a stacked film composed of a stack of group III nitride semiconductor films each containing at least one kind selected from aluminum, gallium, indium, and boron;

wherein,

an upper portion of said stacked film is formed into a ridge-like stripe, to form a current injection region;

a current injection width Wst of said current injection region is at a value in a range of 1 $\mu m \leqq Wst \leqq 3\ \mu m$,

a current non-injection region formed on both sides of said ridge-like strip; ~~and~~

at least part of said current non-injection region is made from a material expressed by a chemical formula $A1_xGa_{1-x}N$ $(0 \leqq x \leqq 1.0)$; ~~and~~

the component ratio "x" of A1 is at a value in a range of $0.3 \leqq x \leqq 1.0$, so that said semiconductor laser light emitting device is configured as an index guide type semiconductor laser light emitting device~~.~~; and

a film located between an active layer and the current non-injection region of the stacked film made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ $(0.3 \leqq x \leqq 1.0)$ and has a thickness of 0.2 μm or less.

3. (Original) A semiconductor laser light emitting device according to claim 1, wherein part, present between an active layer and said current non-injection region, of said stacked film under said current non-injection region at least includes a film which is made from a

material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0.3 \leqq x \leqq 1.0$) and which has a thickness of 0.2 μm or less.

4. (Cancelled)

5. (Original) A semiconductor laser light emitting device according to claim 1, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0.007 \leqq \Delta n = (n1-n2) \leqq 0.012$.

6. (Original) A semiconductor laser light emitting device according to claim 2, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0.007 \leqq \Delta n = (n1-n2) \leqq 0.012$.

7. (Original) A semiconductor laser light emitting device according to claim 3, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0.007 \leqq \Delta n = (n1-n2) \leqq 0.012$.

8. (Original) A semiconductor laser light emitting device according to claim 4, wherein a difference Δn between an effective refractive index n1 of said current injection region

in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0.007 \leqq \Delta n = (n1-n2) \leqq 0.012$.

9. (Currently Amended) A semiconductor laser light emitting device comprising:

a stacked film composed of a stack of group III nitride semiconductor films each containing at least one kind selected from aluminum, gallium, indium, and boron;

wherein,

an upper portion of said stacked film is formed into a ridge-like stripe, to form a current injection region;

a current injection width Wst of said current injection region is at a value in a range of 1 $\mu m \leqq Wst \leqq 3\ \mu m$,

a current non-injection region formed on both sides of said ridge-like strip; and

at least part of said current non-injection region is made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ $(0 \leqq x \leqq 1.0)$; ~~and~~

the component ratio "x" of Al is at a value in a range of $0.15 < x < 0.30$,

so that said semiconductor laser light emitting device is configured as a weak index type pulsation semiconductor laser light emitting device.; and

a film located between an active layer and the current non-injection region of the stacked film made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ $(0.15 \leqq x \leqq 0.30)$ and has a thickness of 0.2 μm or less.

11. (Original) A semiconductor laser light emitting device according to claim 9, wherein part, present between an active layer and said current non-injection region, of said stacked film under said current non-injection region at least includes a film which is made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0.15 \leqq x \leqq 0.30$) and which has a thickness of 0.2 μm or less.

12. (Cancelled)

13. (Original) A semiconductor laser light emitting device according to claim 9, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n1-n2) < 0.007$.

14. (Original) A semiconductor laser light emitting device according to claim 10, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n1-n2) < 0.007$.

15. (Original) A semiconductor laser light emitting device according to claim 11, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n1-n2) < 0.007$.

16. (Original) A semiconductor laser light emitting device according to claim 12, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n1-n2) < 0.007$.

17. (Currently Amended) A semiconductor laser light emitting device comprising:

a stacked film composed of a stack of group III nitride semiconductor films each containing at least one kind selected from aluminum, gallium, indium, and boron;

wherein,

an upper portion of said stacked film is formed into a ridge-like stripe, to form a current injection region;

a current injection width Wst of said current injection region is at a value in a range of 1 $\mu m \leqq Wst \leqq 3\ \mu m$,

a current non-injection region formed on both sides of said ridge-like strip; and

at least part of said current non-injection region is made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ $(0 \leqq x \leqq 1.0)$; ~~and~~

the component ratio "x" of Al is at a value in a range of $0 \leqq x \leqq 0.15$,

so that said semiconductor laser light emitting device is configured as a gain type laser light emitting device.; and

a film located between an active layer and the current non-injection region of the stacked film made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ $(0 \leqq x \leqq 0.15)$ and has a thickness of 0.2 μm or less.

19. (Original) A semiconductor laser light emitting device according to claim 17, wherein part, present between an active layer and said current non-injection region, of said stacked film under said current non-injection region at least includes a film which is made from a material expressed by a chemical formula $Al_xGa_{1-x}N$ ($0 \leqq x \leqq 0.15$) and which has a thickness of 0.2 μm or less.

20. (Cancelled)

21. (Original) A semiconductor laser light emitting device according to claim 17, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n1-n2) < 0.007$.

22. (Original) A semiconductor laser light emitting device according to claim 18, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n1-n2) < 0.007$.

23. (Original) A semiconductor laser light emitting device according to claim 19, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n1-n2) < 0.007$.

24. (Original) A semiconductor laser light emitting device according to claim 20, wherein a difference Δn between an effective refractive index n1 of said current injection region in the film stacking direction and an effective refractive index n2 of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n1-n2) < 0.007$.